circumferential edge of the flat metal rings 494, 496, 400, 402 and the end part of the central metal ring 498 is also 2 mm. The gap between the upper face of the upper bent-back part 404 and the surface of the target 448 is approximately 2 mm.--

IN THE CLAIMS:

Please replace claims 14, 16, 19, and 20 as follows:

14. (Amended) A high frequency sputtering device, comprising:

a processing chamber;

a high frequency power supply;

a cathode inside the processing chamber, the cathode being electrically insulated from the processing chamber and connected to the high frequency power supply, the cathode extending only along a given axial extent of the processing chamber;

a target mounted on a first side of the cathode; and

a metal plate mounted in the processing chamber adjacent to the cathode but in a location outside of the given axial extent of the cathode, the metal plate having an opening in a central portion thereof, wherein an outer circumferential edge of the metal plate is electrically grounded to the processing chamber;

the metal plate is arranged so as to form a gap between the metal plate on the one hand and the cathode and the target on the other hand, wherein the gap is sufficiently narrow and sufficiently long so as to substantially prevent plasma from passing through the gap.

16. (Amended) The high frequency sputtering device as claimed in claim 14, wherein the metal plate is located at a side of the target.

19. (Amended) The high frequency sputtering device as claimed in claim 14, wherein a depth of the gap is greater than or equal to about 3 mm.

20. (Amended) The high frequency sputtering device as claimed in claim 18, wherein a depth of the gap is greater than or equal to about 3 mm.

Please add the following new claims 21 - 26:

--21. The high frequency sputtering device as claimed in claim 14, further comprising a dielectric ring between an outer circumferential surface of the cathode and an inner circumferential surface of the processing chamber, wherein the gap includes:

an axial component defined by a space extending axially between the metal plate and the target, the axial component having an axially extending length, and

a radial component defined by a space extending radially between the dielectric ring and a radial point defined by an inner circumferential surface of the metal plate, the radial component having a radially extending length,

wherein the radially extending length is 3 mm or greater.

22. The high frequency sputtering device as claimed in claim 14, wherein the gap includes a radial component defined by a space extending radially between a radial

point defined by an outer edge of the cathode and another radial point defined by an inner circumferential surface of the metal plate, the radial component having a radially extending length of 3 mm or greater.

23. The high frequency sputtering device as claimed in claim 14, further comprising a dielectric ring between an outer circumferential surface of the cathode and an inner circumferential surface of the processing chamber, wherein the gap includes:

an axial component defined by a space extending axially between the metal plate and the target, the axial component having an axially extending length, and

a radial component defined by a space extending radially between the dielectric ring and a radial point defined by an inner circumferential surface of the metal plate, the radial component having a radially extending length,

wherein the axially extending length and the radially extending length together is 3 mm or greater.

24. The high frequency sputtering device as claimed in claim 14, wherein a width of the gap is less than or equal to 3 mm.

25. The high frequency sputtering device as claimed in claim 14, wherein a depth of the gap is greater than or equal to 3 mm.

26. The high frequency sputtering device as claimed in claim 18, wherein a depth of the gap is greater than or equal to 3 mm.--